# 2.5V Drive Pch MOSFET

# RTL020P02

#### Structure

Silicon P-channel MOSFET

# ● Features

- 1) Low on-resistance. (180m $\Omega$  at 2.5V)
- 2) High power package.
- 3) High speed switching.
- 4) Low voltage drive. (2.5V)

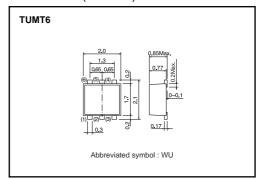
# Applications

DC-DC converter

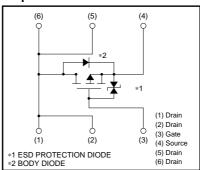
# Packaging specifications

	Package	Taping
Type	Code	TR
	Basic ordering unit (pieces)	3000
RTL020P02		0

# ●Dimensions (Unit:mm)



# ●Equivalent circuit



# ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol		Limits	Unit
Drain-source voltage		V <sub>DSS</sub>		-20	V
Gate-source voltage		V <sub>GSS</sub>		±12	V
Drain current	Continuous	$I_D$		±2	Α
Drain current	Pulsed	I <sub>DP</sub>	*1	±8	Α
Source current	Continuous	Is		-0.8	Α
(Body diode)	Pulsed	I <sub>SP</sub>	*1	-8	Α
Total power dissipation		PD	*2	1	W
Channel temperature	Tch		150	°C	
Range of Storage temperature		Tstg		-55 to +150	°C

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

# ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	125	°C / W

<sup>\*</sup> Mounted on a ceramic board.



# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μΑ	Vgs=±12V, Vps=0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	-20	_	_	٧	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	-1	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-0.7	_	-2.0	٧	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA
Static drain-source on-state resistance	*	-	100	135	mΩ	I <sub>D</sub> = -2A, V <sub>G</sub> s= -4.5V
	R <sub>DS (on)</sub>	-	110	150	mΩ	I <sub>D</sub> = -2A, V <sub>G</sub> s= -4V
		-	180	250	mΩ	I <sub>D</sub> = -1A, V <sub>G</sub> s= -2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	1.2	_	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A
Input capacitance	Ciss	-	430	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	_	80	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	55	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	11	_	ns	ID= -1A
Rise time	tr *	_	13	_	ns	V <sub>DD</sub> ≒ −15V
Turn-off delay time	t <sub>d (off)</sub> *	_	38	_	ns	V <sub>GS</sub> = -4.5V R <sub>L</sub> =15Ω
Fall time	t <sub>f</sub> *	-	12	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	4.9	_	nC	V <sub>DD</sub> ≒−15V R <sub>L</sub> =7.5Ω
Gate-source charge	Q <sub>gs</sub> *	_	1.2	_	nC	V <sub>GS</sub> = -4.5V R <sub>G</sub> =10Ω
Gate-drain charge	Q <sub>gd</sub> *	-	1.3	-	nC	I <sub>D</sub> = -2A

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	_	-1.2	V	I <sub>S</sub> = -0.8A, V <sub>GS</sub> =0V

# Electrical characteristic curves

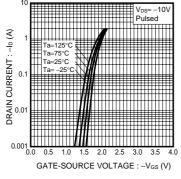


Fig.1 Typical Transfer Characteristics

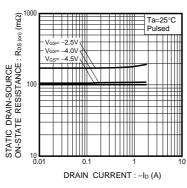


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

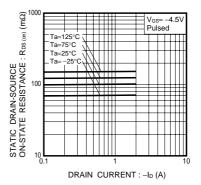


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

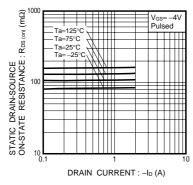


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

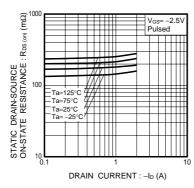


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

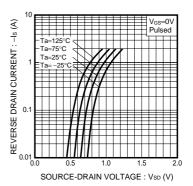


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

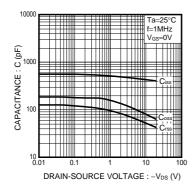


Fig.7 Typical Capacitance vs. Drain-Source Voltage

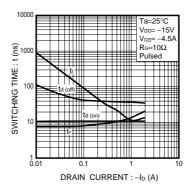


Fig.8 Switching Characteristics

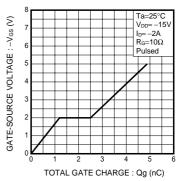


Fig.9 Dynamic Input Characteristics

# Measurement circuits

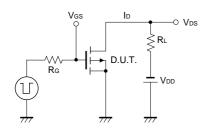


Fig.10 Switching Time Measurement Circuit

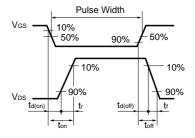


Fig.11 Switching Waveforms

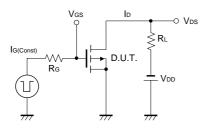


Fig.12 Gate Charge Measurement Circuit

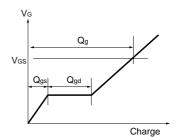


Fig.13 Gate Charge Waveforms

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